



## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

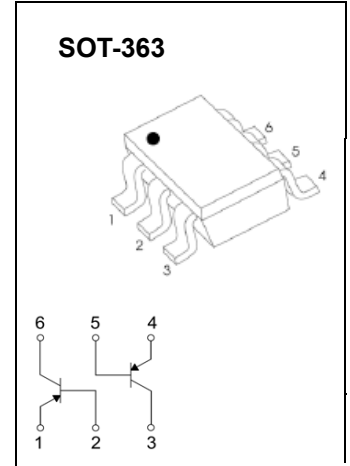
### FEATURES

- Complementary to MMDT5551DW
- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching

MARKING: 2L

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

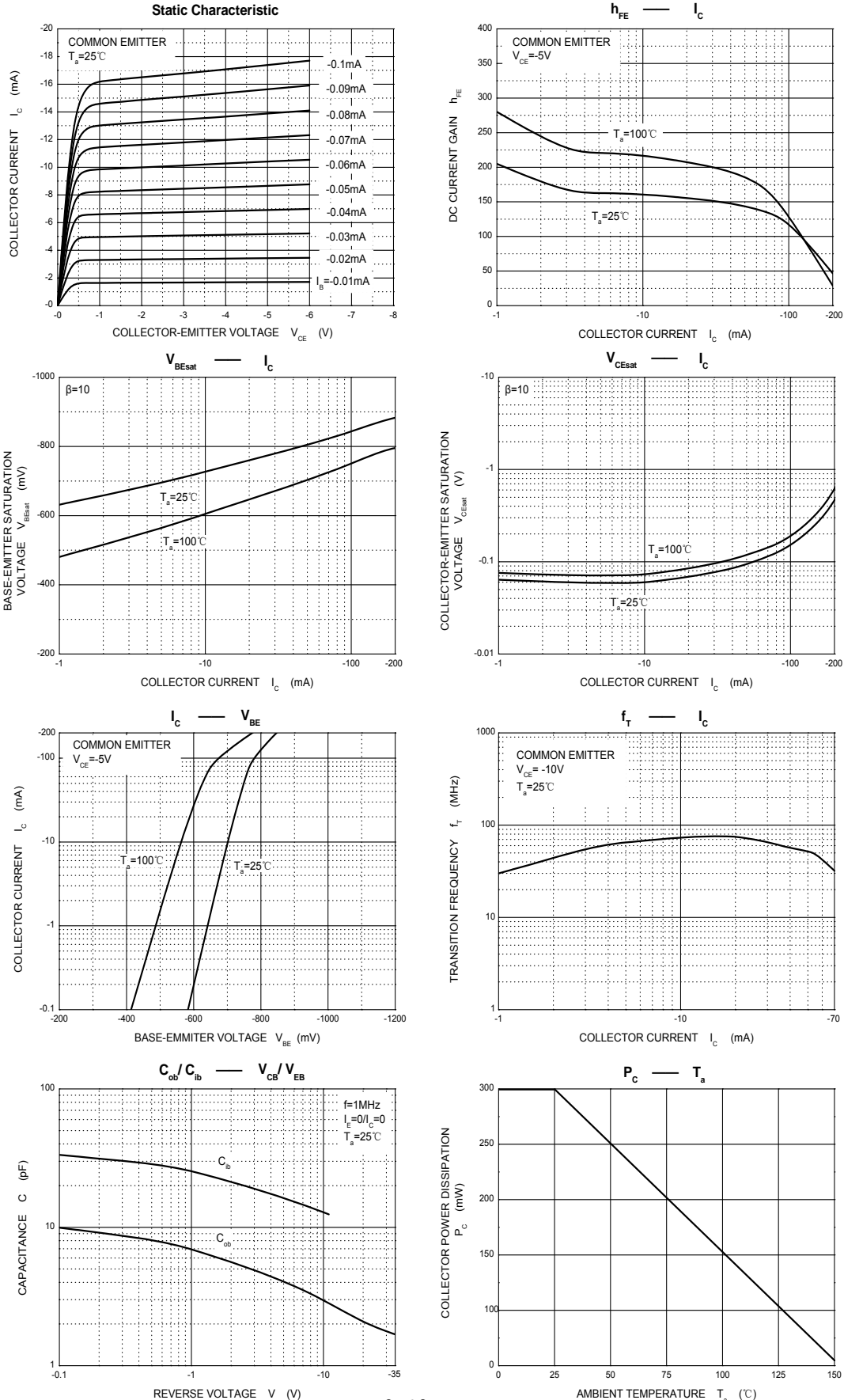
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-150	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-600	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C



### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

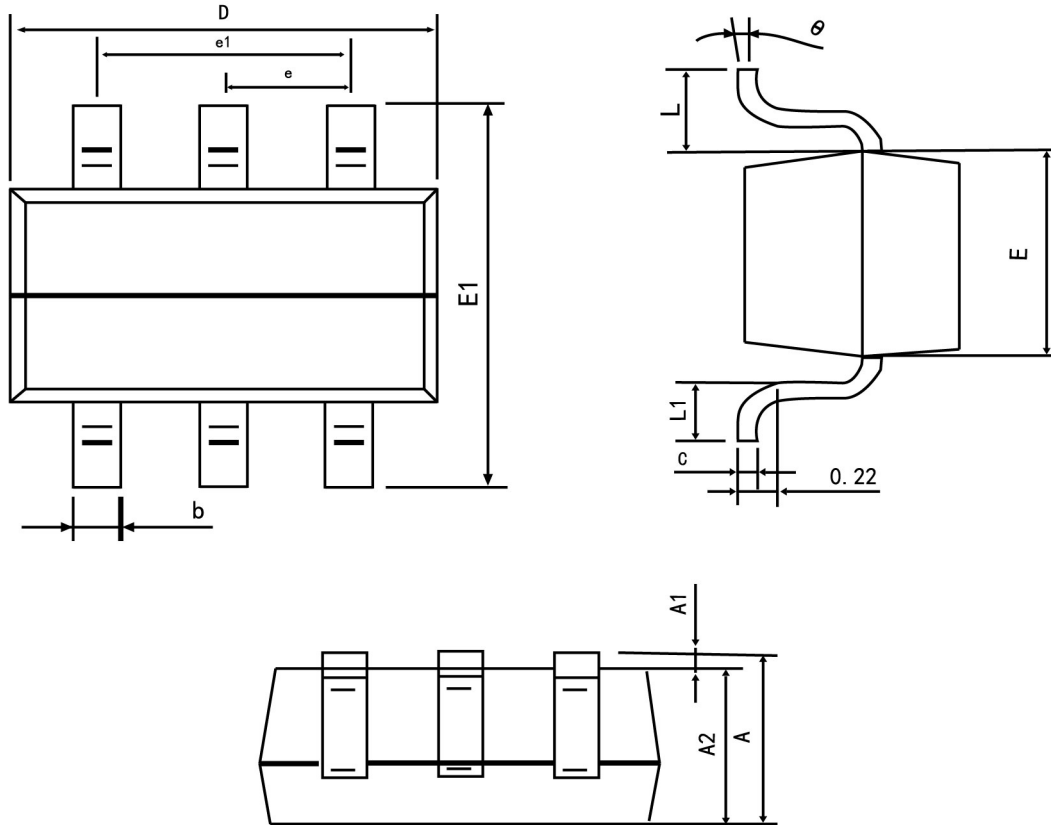
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-160			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-150			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>C</sub> =0			-50	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	50			
		V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	60		300	
		V <sub>CE</sub> =-5V, I <sub>C</sub> =-50mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.5	V
		I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-1	V
		I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA, f=100MHz	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz			6	pF

### Typical Characteristics





## SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°

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